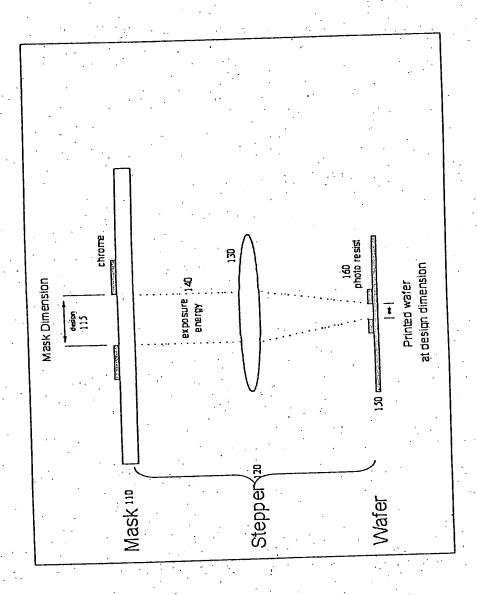
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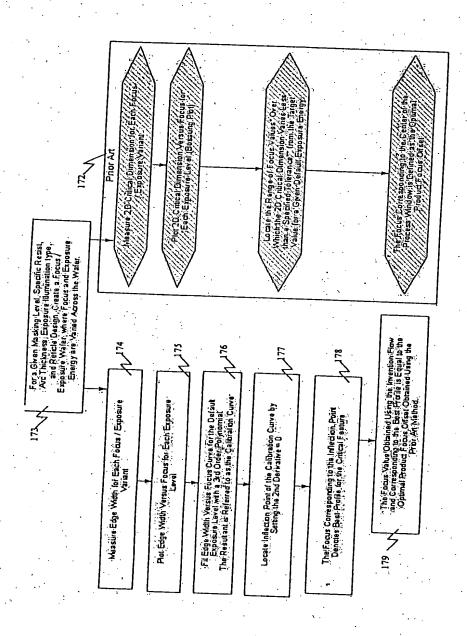


Fig. 1A

1

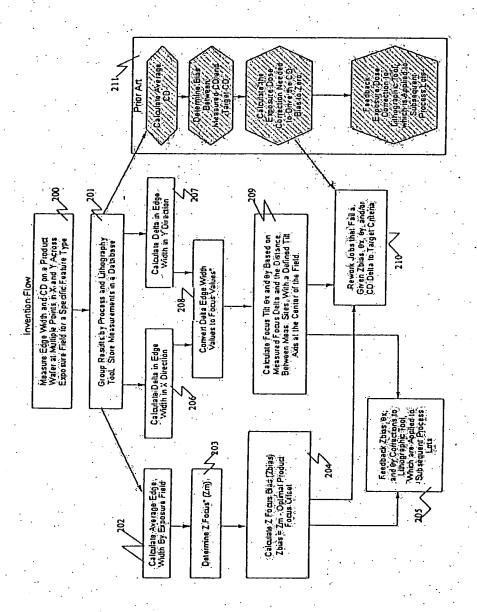


Fig. 1B

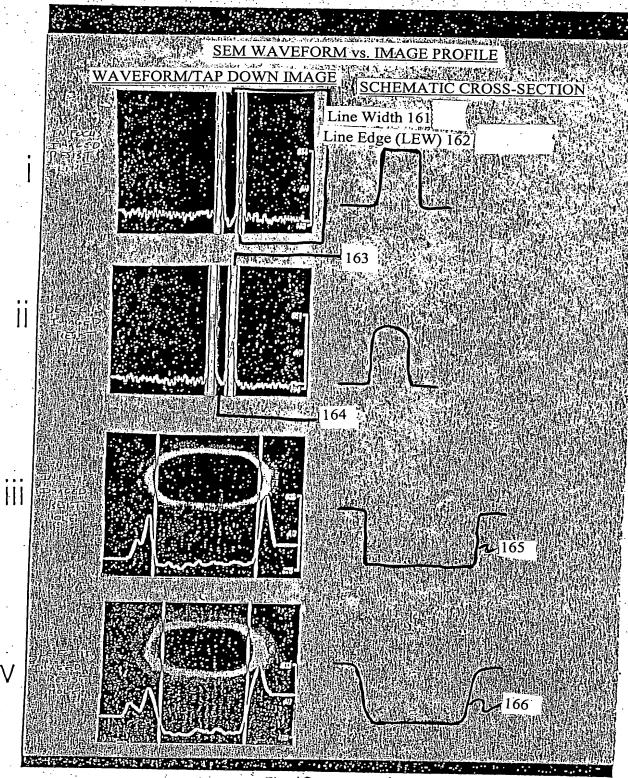


Fig. 1C

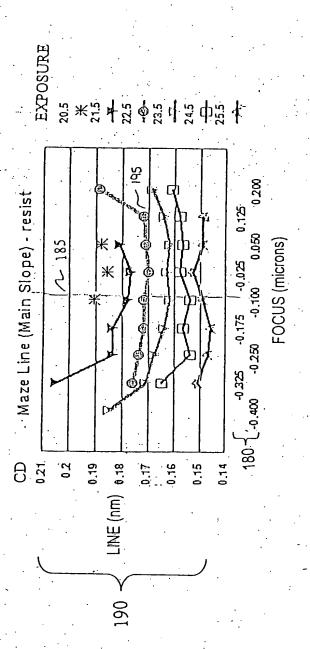


Fig. 1D

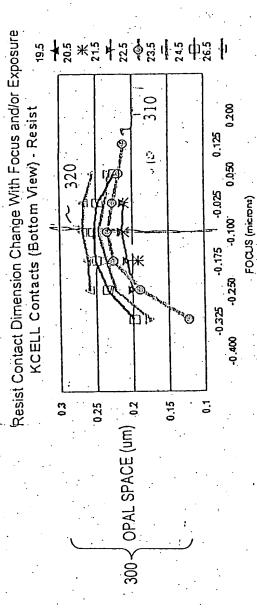
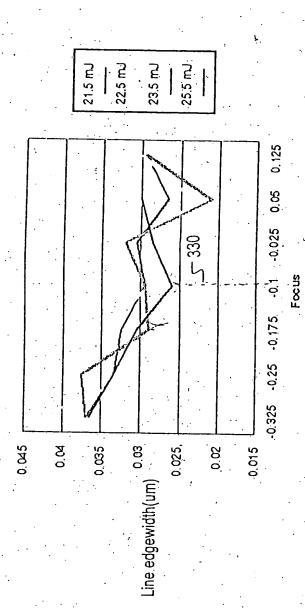


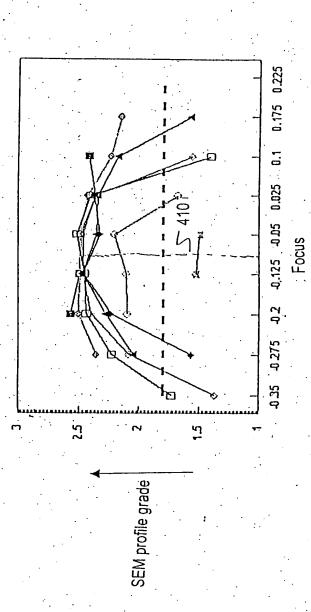
Fig. 2



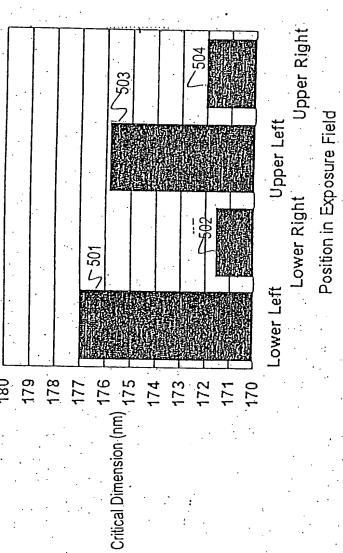
THE REPORT OF THE PARTY OF THE

Fig 3





Critical Dimension of Imaged Photoresist as Measured by CD



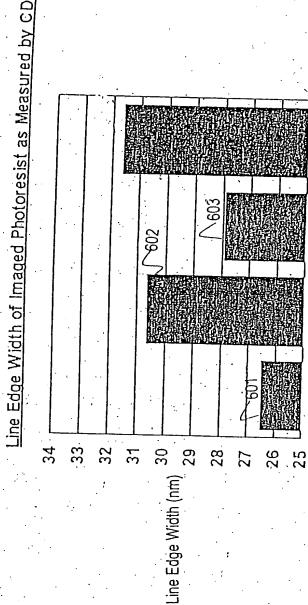


Fig. 6

Upper Right

Position in Exposure Field

Lower Left Lower Right U

X/Y Tilt Determination Using Edge Width Measurement 32 Line Edge Width (nm) 30 . 26 28 33 3 27

Fig. 7

Avg Upper EW Avg Right EW Avg Lower EW Avg Left EW

25.

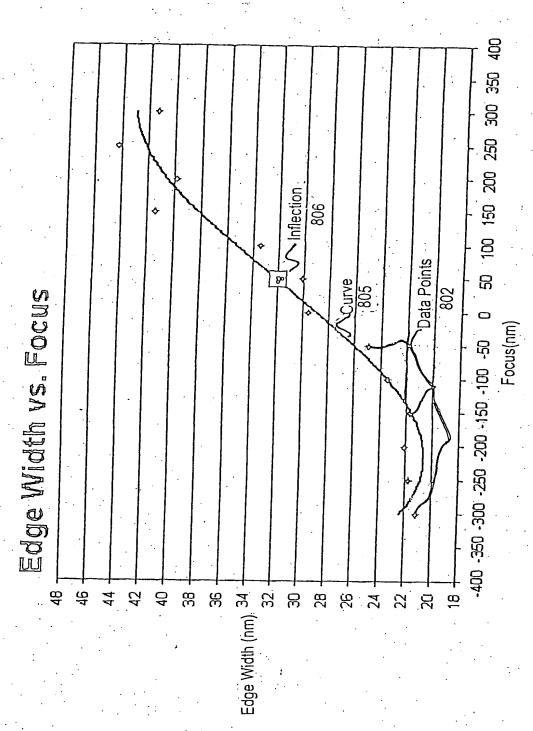
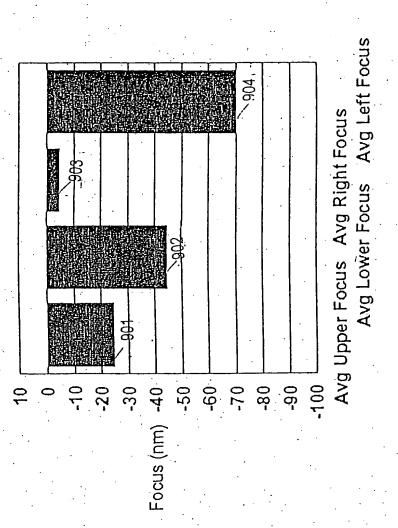
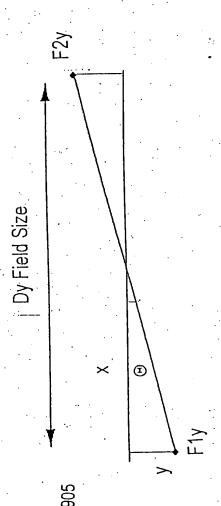


Fig. 8

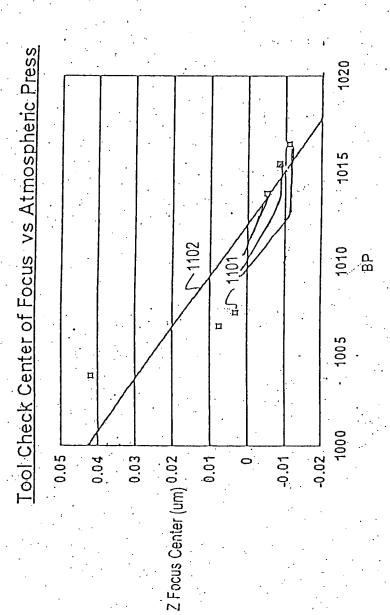
X/Y Tilt Determination Using Edge Width Measurement

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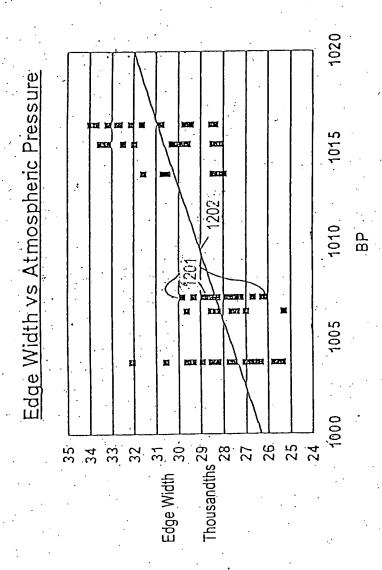


Fig. 12

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TABLE OF RUN RULES

1310 Tool	1320 Technology	1330 WaferPN	1340 Process	1350 Opt	1360 Default Exposure	1370 Focus
U82V	ICE8S3D	*	мс	F	19.00	0.18
U82V	ICECBS2	*	мс	F	19.00	6.18 .
U82V	ICEC8S3	*	мс	E	19.98	8.18
U84V	CM0S6X1	*	MC	F	28.88	6.66
U86V	CS01950	* .	MC9S	F.	24.00	-0.19
V86V	CS019S8	9899898J8648	MC9S	F	30.00	-0.18
U86V	CSOISS	0000008J0645	MC9S	F.	38.88	-8.18
V86V	CS019S8	,0000057P6438	MC9S	F	28.00	-8.05
Vasu	CS019S2	*	MC9S	F	25.88	-8.10
U92V	CS019S8	*	MC9S -	F	24	-0.10
U92V	CS019S8 ·	9999988J9639	MC9S	E	30.00	-8.18
U92V	CS019S0	0000008J0640	MC9S	F.	38.88	-0.10

Fig. 13 (Prior Art)

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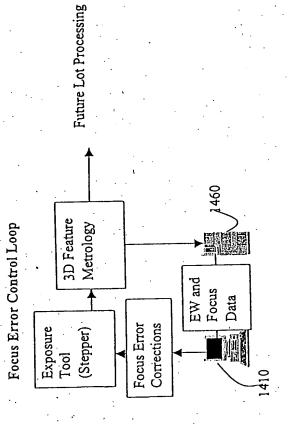


Fig. 14